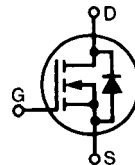


Standard Power MOSFET

IXTH / IXTM 5N100
IXTH / IXTM 5N100A

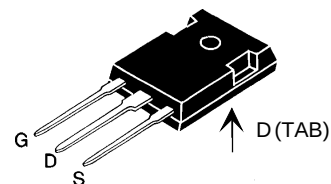
V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	5 A	2.4 Ω
1000 V	5 A	2.0 Ω

N-Channel Enhancement Mode

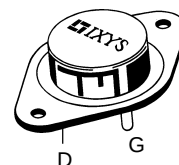


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	5	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	20	A
P_D	$T_C = 25^\circ\text{C}$	180	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXTH)



TO-204 AA (IXTM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
 - easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

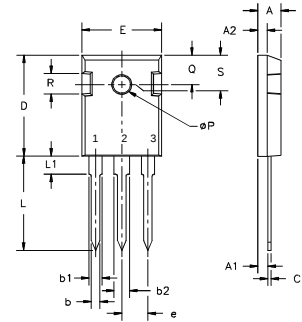
Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$			250 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ }I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			2.4 Ω 2.0 Ω

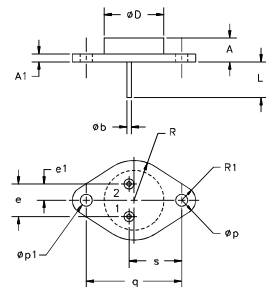
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 \cdot I_{D25}$, pulse test	4	6	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		2600	pF
C_{oss}			180	pF
C_{rss}			45	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 I_{D25}$ $R_G = 4.7\ \Omega$, (External)		35	100 ns
t_r			20	50 ns
$t_{d(off)}$			100	200 ns
t_f			30	80 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 I_{D25}$		88	130 nC
Q_{gs}			21	30 nC
Q_{gd}			38	70 nC
R_{thJC}				0.7 K/W
R_{thCK}		0.25		K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			5 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			20 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$		900	ns

TO-247 AD (IXTH) Outline


Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L1	4.50	.177
ØP	3.55 3.65	.140 .144
Q	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

TO-204AA (IXTM) Outline


Pins 1 - Gate 2 - Source
Case - Drain

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	6.4 11.4	.250 .450
A ₁	3.42	.135
Øb	.97 1.09	.038 .043
ØD	22.22	.875
e	10.67 11.17	.420 .440
e ₁	5.21 5.71	.205 .225
L	7.93	.312
Øp	3.84 4.19	.151 .165
Øp ₁	3.84 4.19	.151 .165
q	30.15 BSC	1.187 BSC
R	13.33	.525
R ₁	4.77	.188
s	16.64 17.14	.655 .675

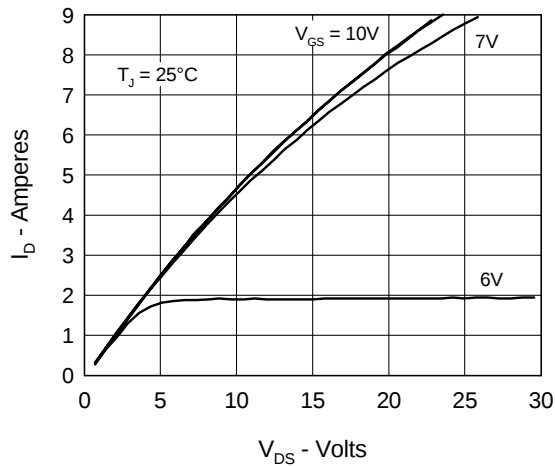
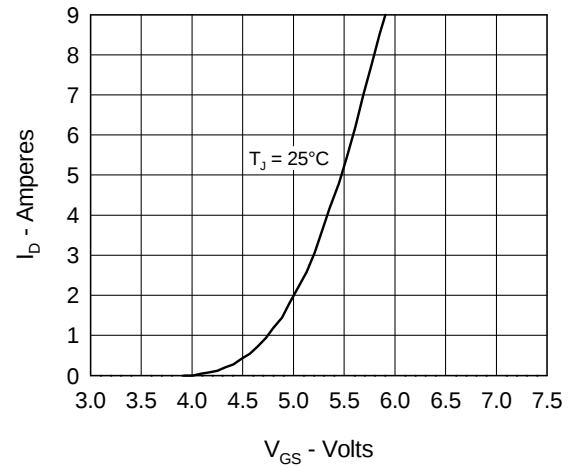
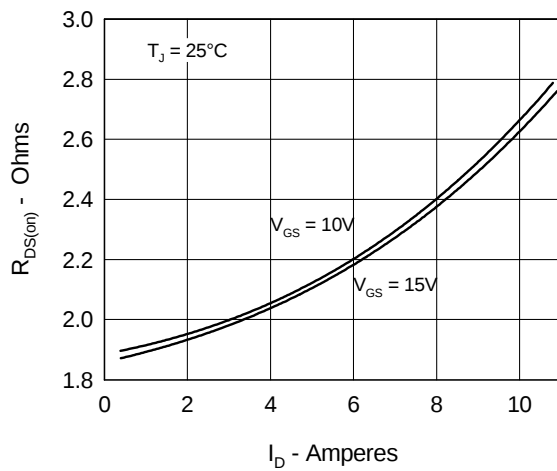
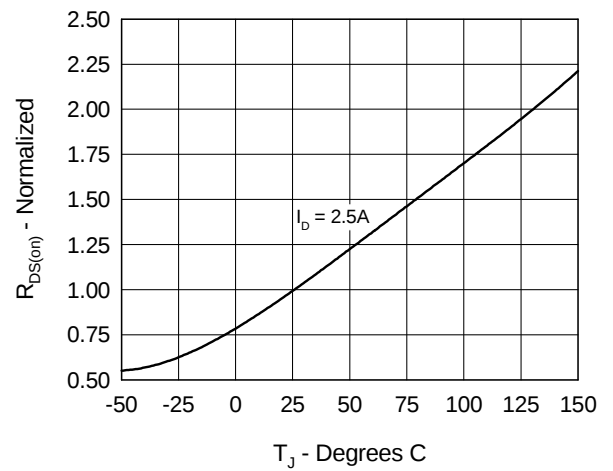
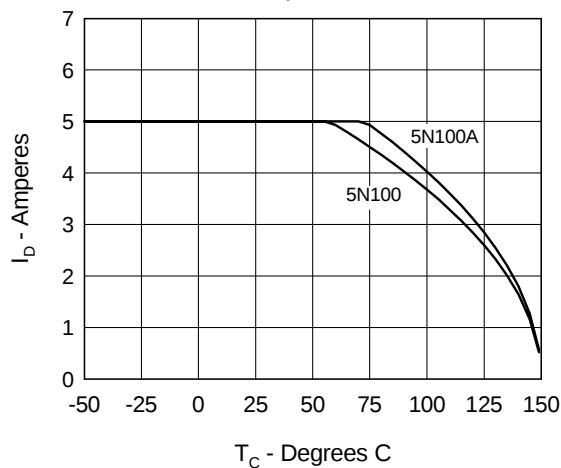
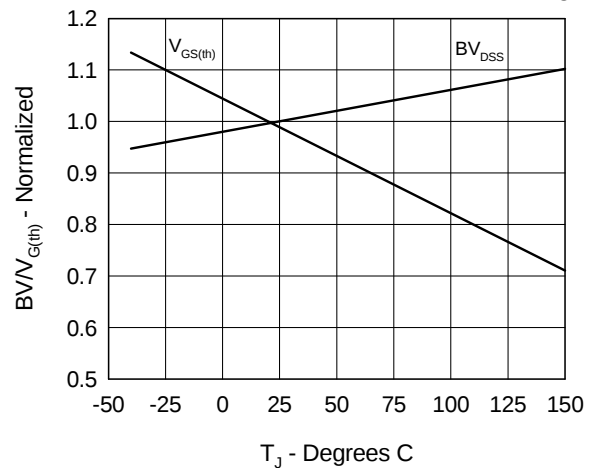
Fig. 1 Output Characteristics

Fig. 2 Input Admittance

Fig. 3 $R_{DS(on)}$ vs. Drain Current

Fig. 4 Temperature Dependence of Drain to Source Resistance

Fig. 5 Drain Current vs. Case Temperature

Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Gate Charge Characteristic Curve

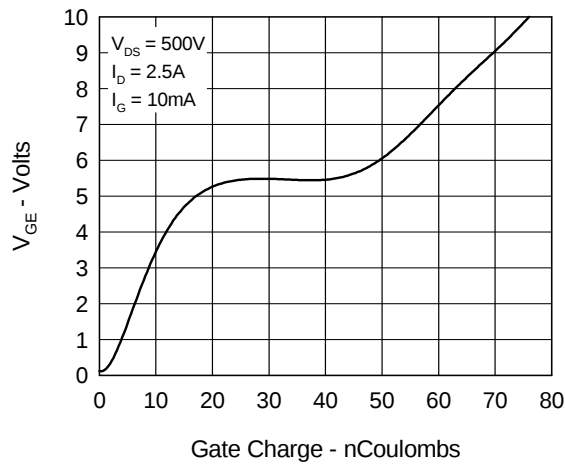


Fig.8 Forward Bias Safe Operating Area

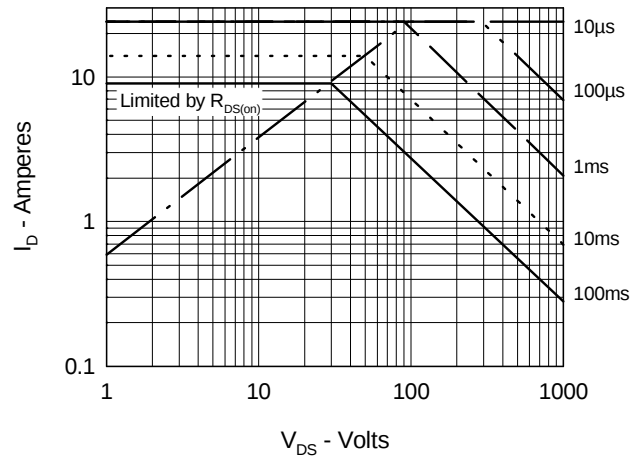


Fig.9 Capacitance Curves

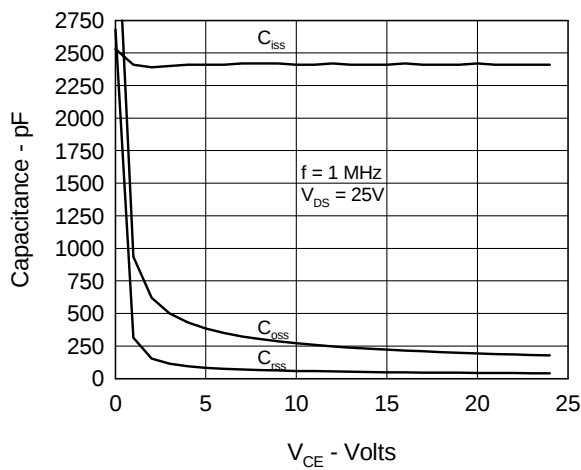


Fig.10 Source Current vs. Source to Drain Voltage

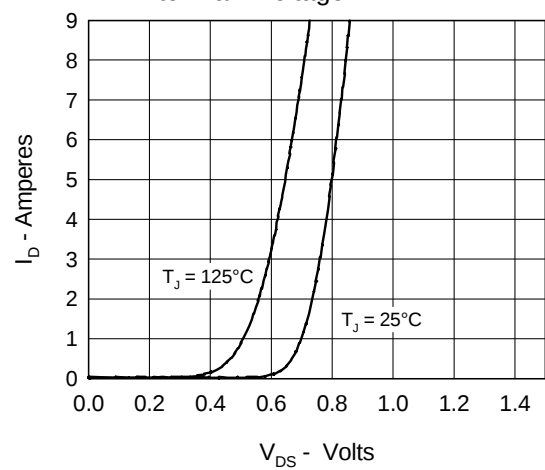


Fig.11 Transient Thermal Impedance

